

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination 09/684,904 KON ET AL.	
	Examiner Dana Farahani	Art Unit 2814	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5874750	02-1999	Yanagisawa et al.	257/133
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Takeda et al., 1200V Trench gate NPT-IGBT (IEGT) with Excellent Low On-State Voltage, Power Semiconductor Devices and ICs, 1998. ISPSD 98. Proceedings of the International Symposium on, 1998, PP. 75-79
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.